

Cr-Si-C-BASED SINTERED BODY

ABSTRACT

An object of the present invention is to provide a high-density Cr-Si-C-based sintered body including chromium (Cr), silicon (Si) and carbon (C) and is furthermore to provide at least one of the high-density Cr-Si-C-based sintered body, a sputtering target including the sintered body or a method for producing a film using the sputtering target. The present invention can provide a Cr-Si-C-based sintered body including chromium (Cr), silicon (Si) and carbon (C), wherein the sintered body has a relative density of 90% or more and a porosity of 13% or less.

[No Suitable Figure]